



# Experiments and modelling for glow discharge plasmas applied to sputter deposition in superconducting radiofrequency cavities

*Review of PhD first year*

Thibaut Richard (CERN – EPFL/SPC)

Thesis directors : Ivo Furno (EPFL/SPC) – Alban Sublet (CERN/TE-VSC-SCC)

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# Outline

## I. Context and objectives

1. Thin-film coating for SRF cavities
2. Motivation for numerical simulations

## II. First results

1. Experimental system
2. Study of sputtered atoms transmission
3. First plasma simulations

## III. Future experimental upgrades and simulation plan

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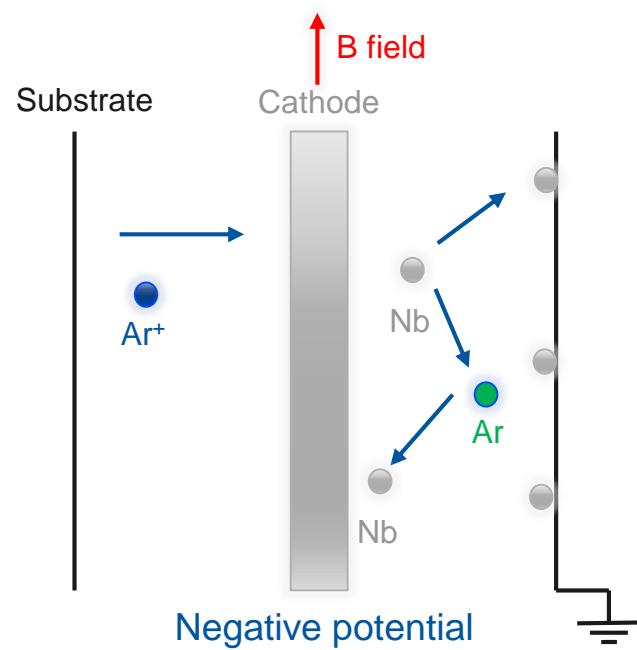
# Thin-film coating for SRF cavities

- Superconductive Radio-Frequency cavities used for particle beam acceleration
- Study focused on niobium-on-copper thin film coating
- Different plasma-based sputtering techniques used :
  - DC diode
  - DC magnetron



# Principle of plasma-based sputtering

- Sputtering : removal of atoms from a target by particle bombardment
- In our case, the sputtering source is the ions from the glow discharge plasma
- For rotational symmetry geometries (e.g. tubes, some RF cavities...), a cylindrical electrode configuration is desirable



DC cylindrical diode

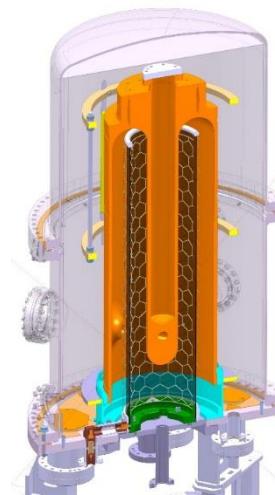
- No magnetic field
- “High” pressure
- Low deposition rate

DC cylindrical magnetron

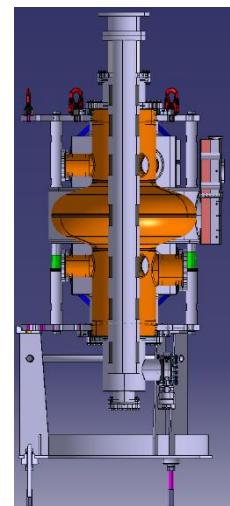
- Axial magnetic field
- Lower pressure
- Higher deposition rate
- **B** : increase electron path before collection on electrodes

# Motivation for numerical simulations

- Optimize the coating parameters while reducing the R&D trial-and-error phase:
    - Uniformity of film thickness on different complex geometries
    - Bombardment of particles...
    - ... and energy/angle of sputtered atoms influencing the film growth
- Numerical modelling from plasma generation to niobium transport



HIE-ISOLDE type



LHC type

# Approach

Experiment

Input parameters :

- Given geometry, e.g. SRF cavity
- Pressure
- Power
- *Magnetic field* ...

Simulation

Physics

Numerical model

- Electromagnetic solver
- Particle “pusher”
- Reactions on surfaces and in buffer gas ...

Outputs

- Plasma characteristics (density, impedance, ...)
- Thin film characteristics (thickness, morphology, ...)

Benchmarking of the numerical model  
on a simple geometry

Prediction for real complex geometries

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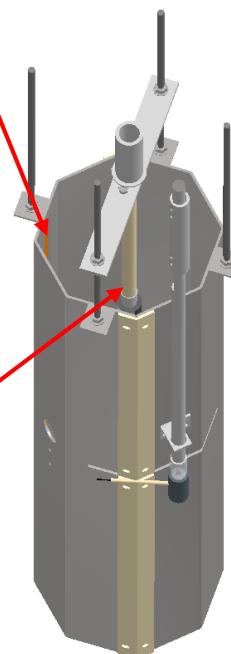
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# Experimental System

Aim : provide data for comparison with simulations

Copper strip for thickness profile



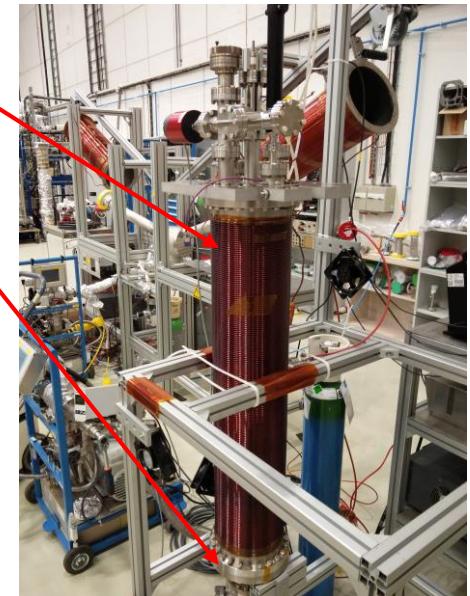
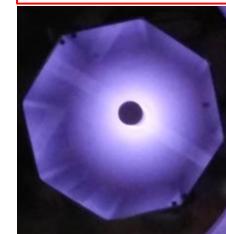
Niobium cathode  
(303 mm length)  
• DC bias diode  
• DCMS

Octagonal anode  
(500 mm height)



UHV chamber  
with solenoid

Viewport



*Installed in building 181*

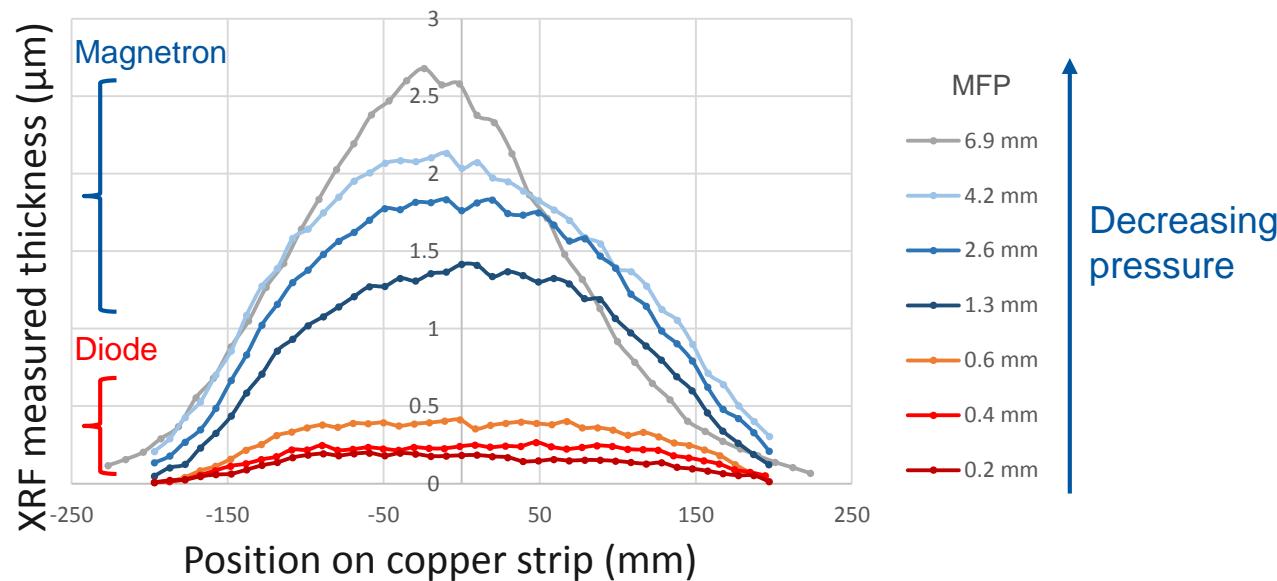
Instruments:  
RFEA (ion energy on substrate)  
Quartz balance (deposition rate)

Langmuir probe (plasma density)

And current / voltage probes

# Study of sputtered atoms transmission: experiment

- Aim : evaluate the effect of collisions (i.e. pressure) on niobium transport and compare with simulations
- Input parameters:
  - Constant power (100 W) and coating time (5 hours)
  - 7 different pressures (from  $1,5 \cdot 10^{-2}$  mbar to 0.65 mbar)
- Conversion of pressure into mean free path of niobium sputtered atoms in the argon buffer gas
  - $mfp = \frac{4k_B T}{\pi \sqrt{2} P (\delta_{Nb} + \delta_{Ar})^2} \propto \frac{1}{P}$



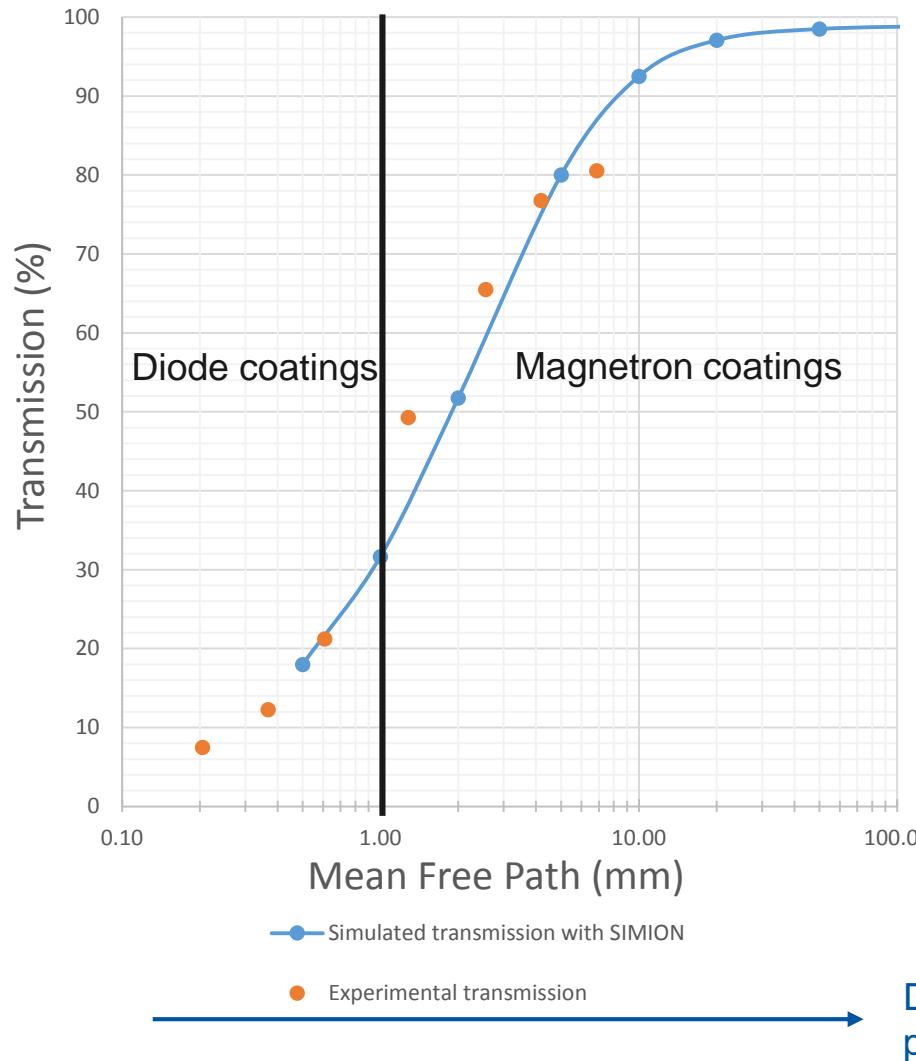
# First approach on numerical modelling

- SIMION software : atom transport with **hard-spheres binary collisions model**
- Simulation inputs :
  - Geometry
  - Argon buffer gas and sputtered niobium atomic masses
  - Mean free path
  - Cosine emission angular distribution
  - Uniform sputtering flux along cathode with  $E_{\text{initial}} = 5 \text{ eV}$
- Simulation output : transmission of sputtered atoms with respect to mfp

- Conversion of experimental thickness profiles to transmission percentage

$$\text{Transmission} = \frac{\text{Number of deposited atoms}}{\text{Number of sputtered atoms}} \propto \frac{\text{film thickness}}{\text{current} \times \text{time}}$$

# Study of sputtered atoms transmission



- Pressure ↓: transmission ↑
  - First approach: transport only
- Next step: plasma modelling

# First plasma simulations: simulation code

- PICMC/DSMC<sup>1</sup> parallel computing code from Fraunhofer Institute (Braunschweig) acquired in September 2015
  - Plasma simulation module
  - Gas flow and neutral transport module
    - Statistical method for solving the Boltzmann equation
    - Especially suited for rarefied gas flows where fluid models do not apply
  - Different time scales for plasma and transport: decoupling of the two
- Installed on CERN Linux server (10 nodes of 16 CPU each)
- Quite resource demanding :
  - 3D Plasma simulation of experimental system = 1 week for 10  $\mu$ s on 144 CPU

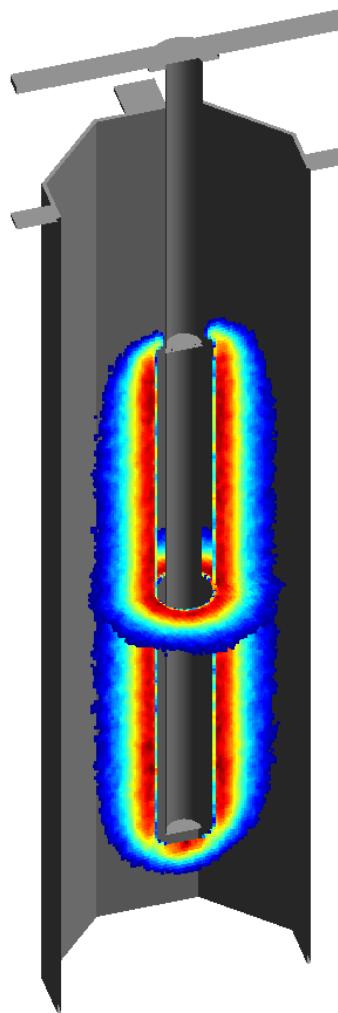
<sup>1</sup> Particle-in-Cell Monte Carlo/Direct Simulation Monte Carlo  
<http://www.ist.fraunhofer.de/en/services/simulation.html>



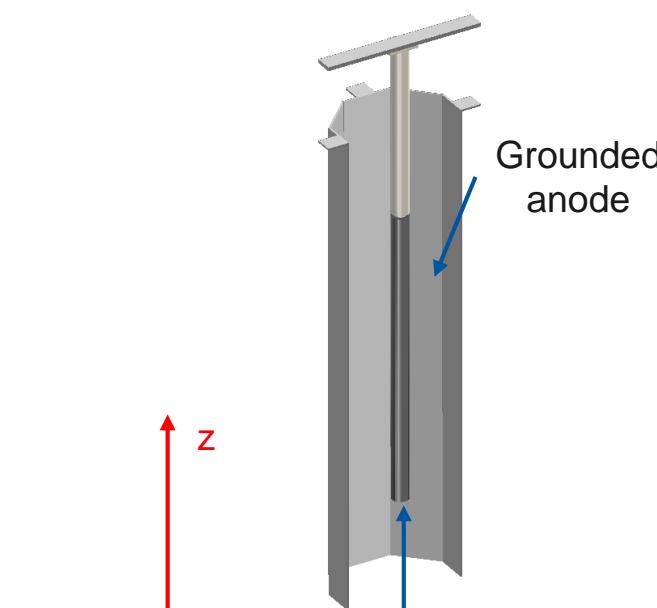
# Plasma module: electron density ( $\text{m}^{-3}$ )

Electron density (1/CubicMeter)

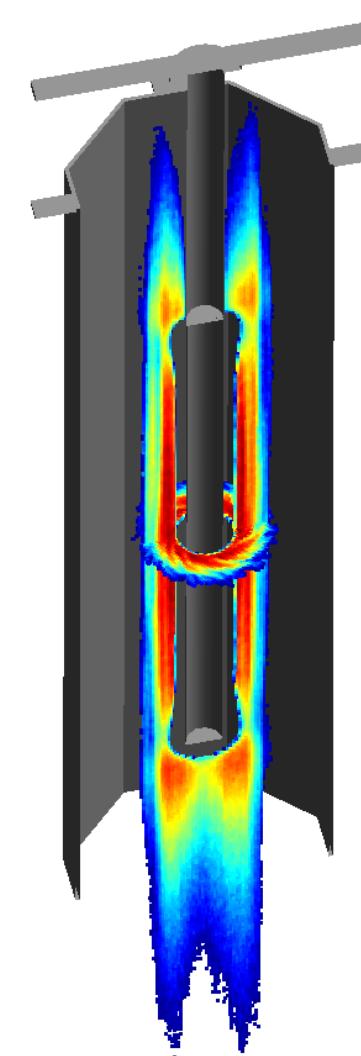
3.16e+14 3.98e+14 5.01e+14 6.3e+14 7.94e+14 9.98e+14 1.26e+15 1.58e+15 1.99e+15 2.51e+15 3.16e+15



DC diode at 0.3 mbar

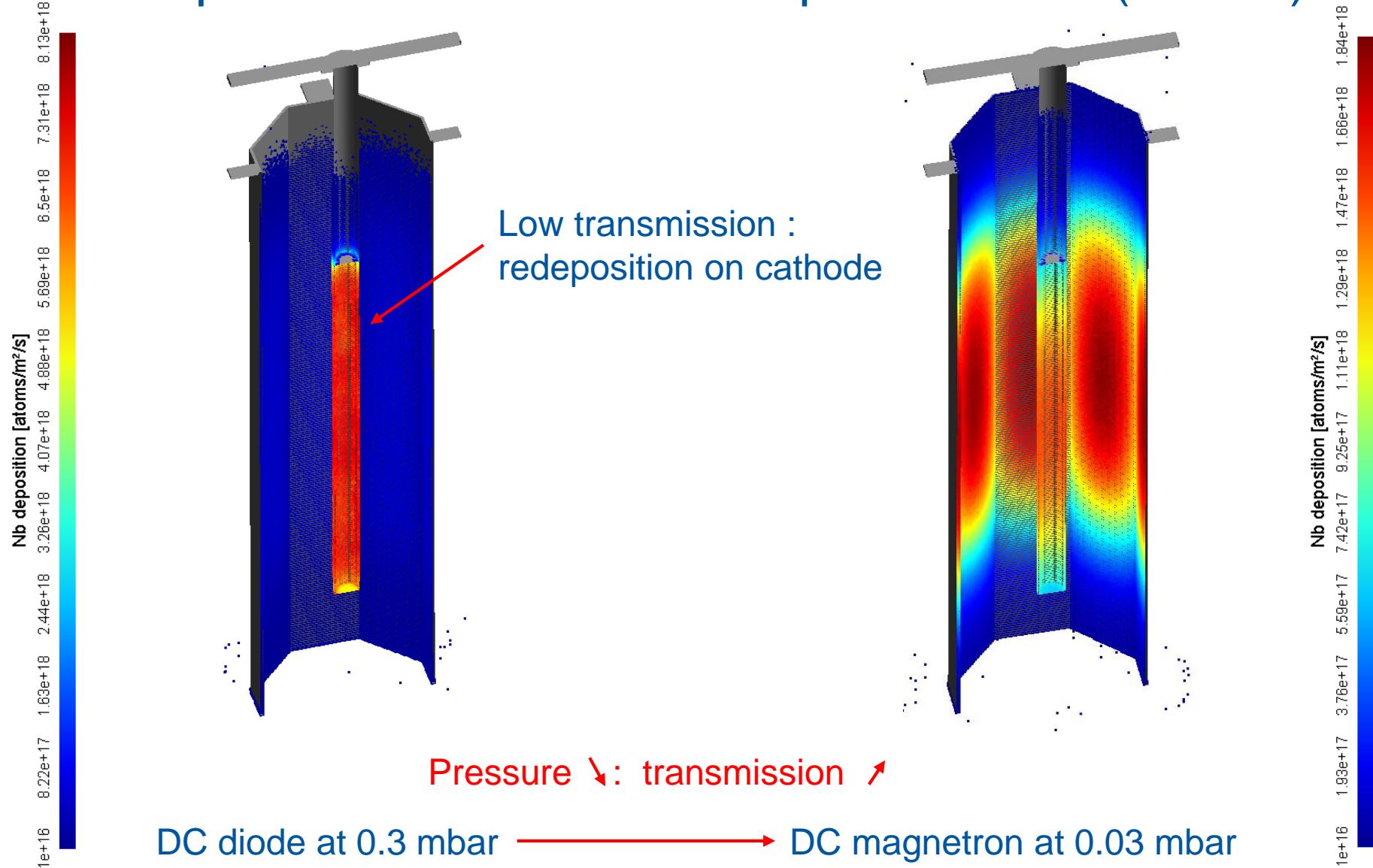


10 watts

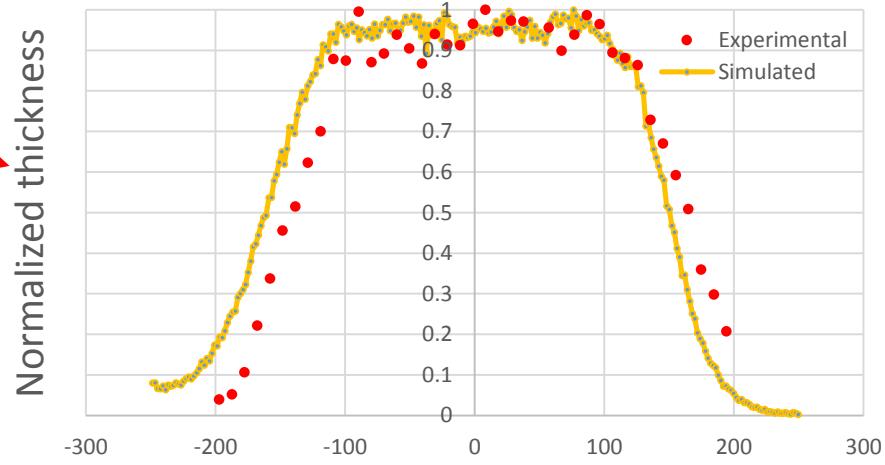
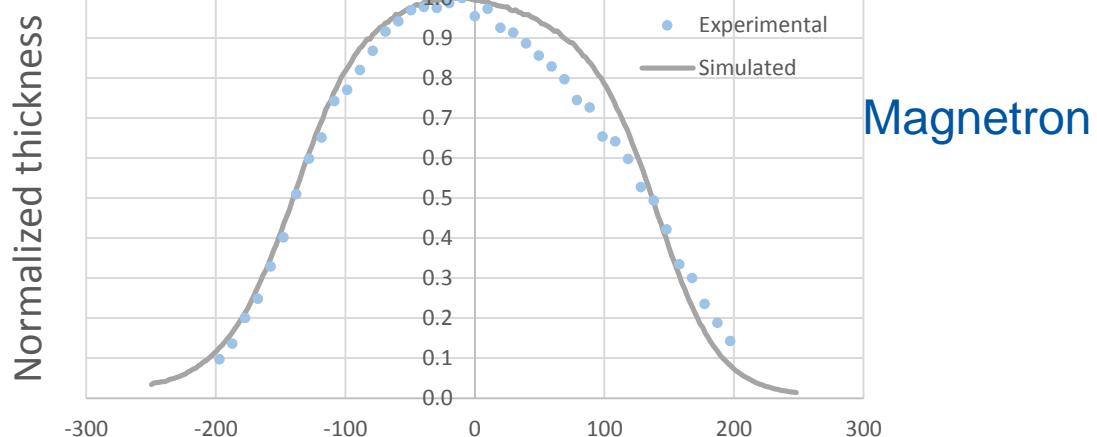
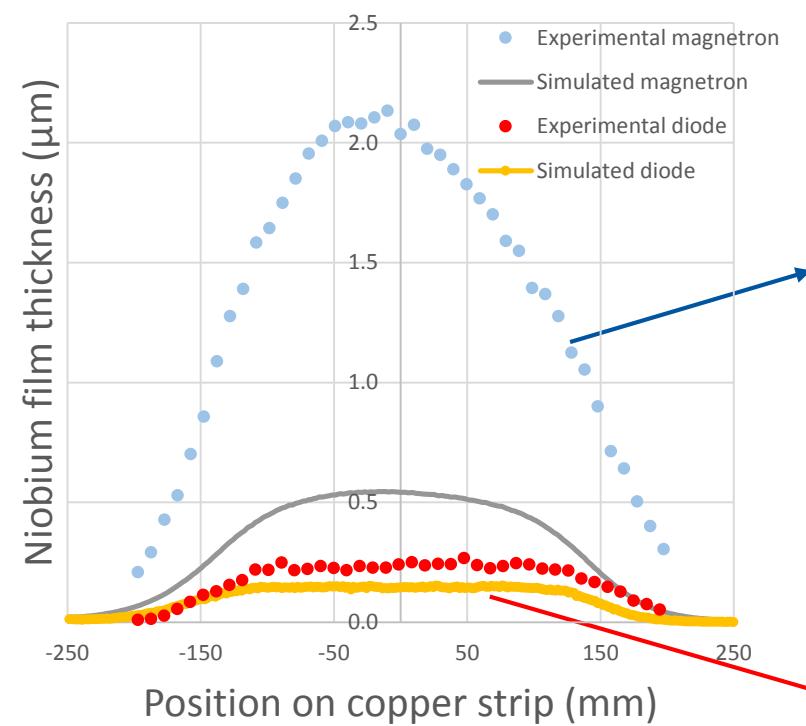


DC magnetron at 0.03 mbar

# Transport module: niobium deposition flux (#/m<sup>2</sup>/s)



# First plasma simulations: niobium thickness profiles



Magnetron

Diode

	Simulation	Experiment
Power (W)	10	100
Sputtering yield	1	$Y = f(E, \theta) < 1$



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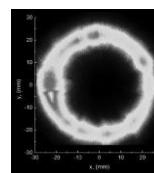
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# Future experimental upgrades and simulation plan

- Experimental upgrades:
  - Langmuir probe: plasma density, electronic temperature
  - Retarding field energy analyser: ion energy distribution on the substrate
  - Intensified high speed camera: spatial resolution of plasma features (spirals in magnetron ?)
- Simulation benchmarking:
  - Validation of physical model including sputtering yield =  $f(E, \theta)$
  - Influence and scale-up of discharge power
- Model real cavities:
  - HIE-ISOLDE (single and double cathode with grids and bias)
  - Elliptical type

<sup>1</sup> From A. Anders *et al.*, *Drifting localization of ionization runaway: Unraveling the nature of anomalous transport in high power impulse magnetron sputtering*, J. Appl. Phys. **111**, 053304 (2012)

# Summary

- The objective is to model glow discharge plasma sputtering for thin-film coatings
- The current phase consists in benchmarking a simulation code on a simple experimental setup equipped with several diagnostic instruments
- The future plan will be to model real complex SRF cavities coating processes

# Thank you for your attention!

*Acknowledgements to:  
TE-VSC-SCC section*





[www.cern.ch](http://www.cern.ch)

## Evaluation of experimental number of deposited atoms

*Number of deposited atoms*

$$= \frac{NbDensity * FilmThickness * XRFstep * CumulatedAnodeWidth * N_A}{NiobiumMolarMass}$$

Boltzmann Equation

$$\frac{\partial f}{\partial t} + \mathbf{v} \cdot \frac{\partial f}{\partial \mathbf{x}} + \frac{q}{m} (\mathbf{E} + \mathbf{v} \times \mathbf{B}) \cdot \frac{\partial f}{\partial \mathbf{v}} = \left( \frac{\partial f}{\partial t} \right)_{coll}$$

Where  $f(\mathbf{x}, \mathbf{v}, t)$  is the particles distribution function

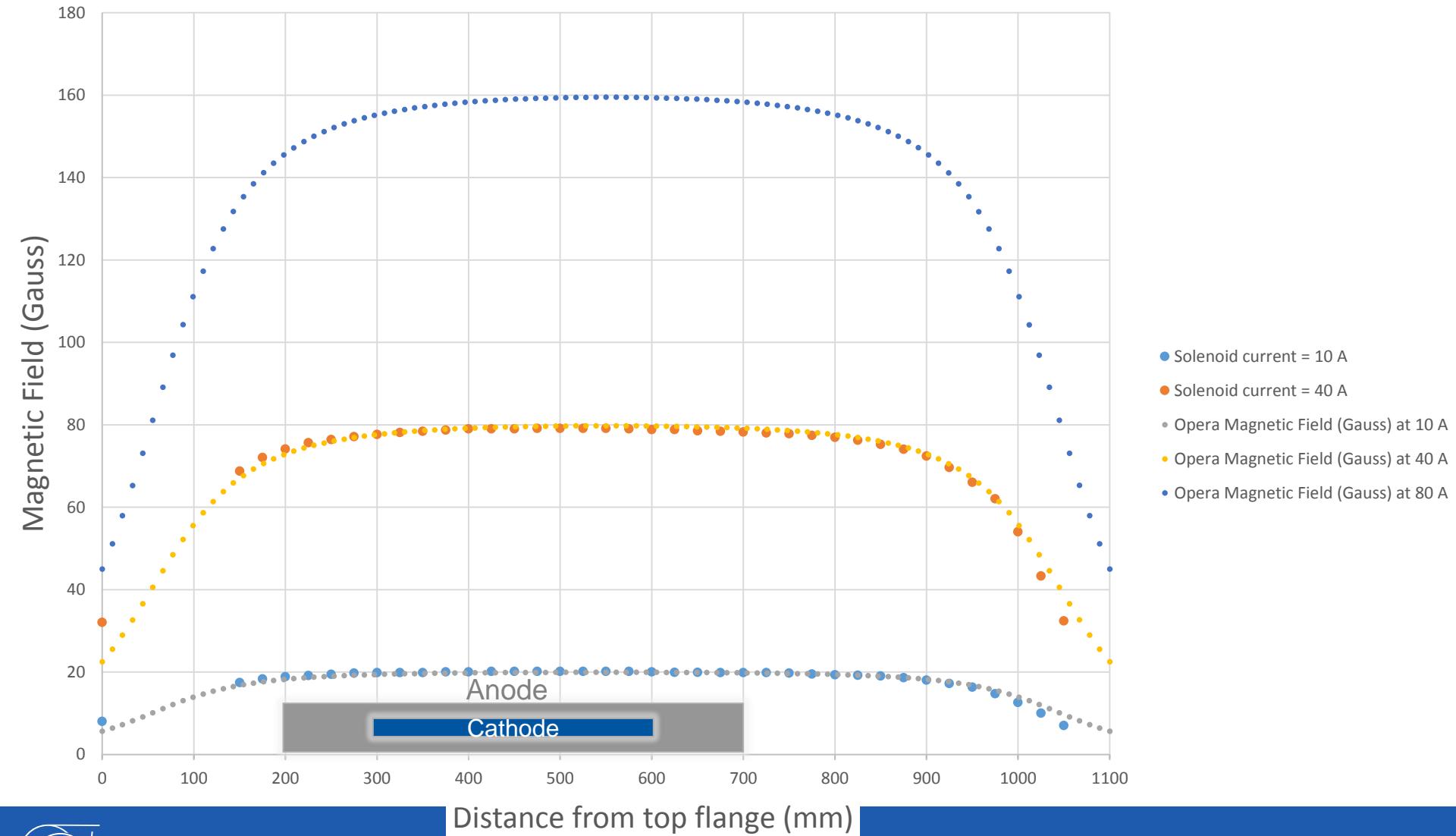
Conversion of niobium absorption to film growth rate

$$Film\ growth\ rate\ (nm/s) = \frac{Absorption(\#/m^2/s) * NiobiumMolarMass(\frac{g}{mol}) * 10^3}{NiobiumVolumicMass\left(\frac{g}{cm^3}\right) * N_A(\frac{1}{mol})}$$

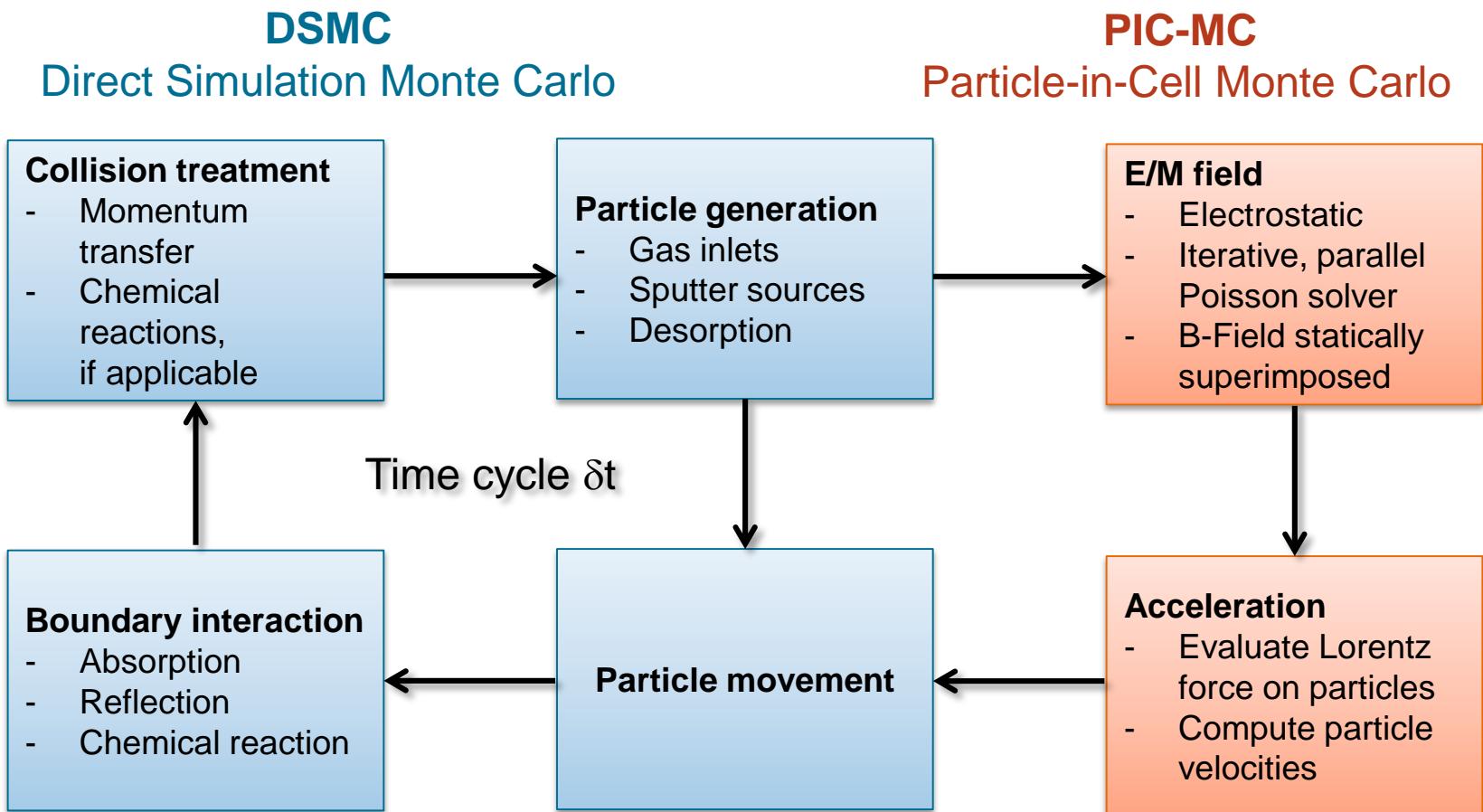


# Magnetic field homogeneity

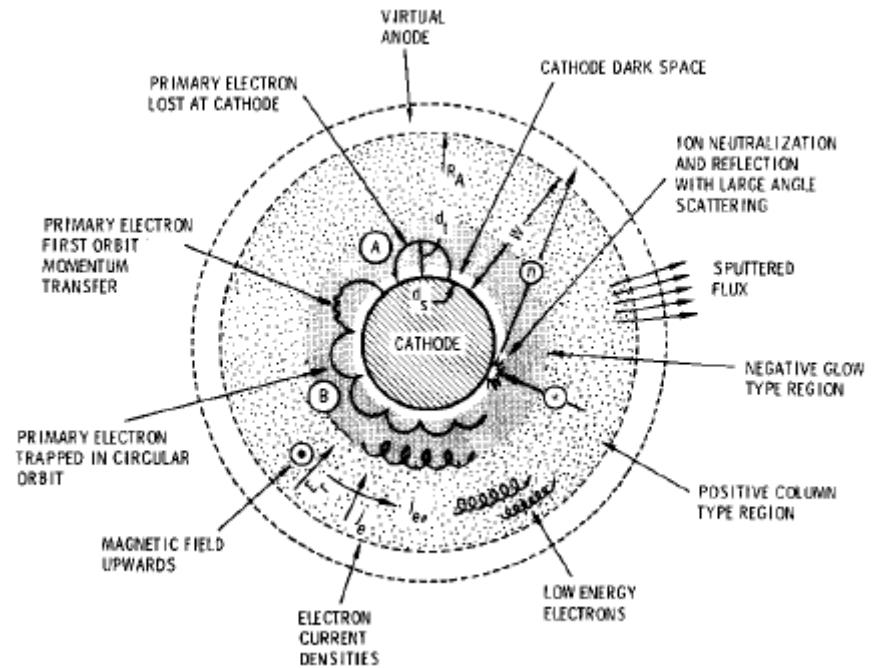
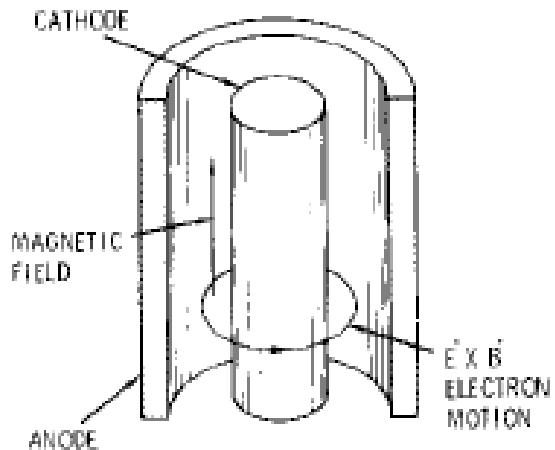
Measured  $B$  (Gauss)  $\sim 2 \cdot I_{\text{coil}}$  (A)



# DSMC/PIC-MC method



# Electron trajectories in cylindrical magnetron



From J.A. Thornton, *Magnetron sputtering: basic physics and application to cylindrical magnetrons*,  
J. Vac. Sci. Technol. **15**, 171-177 (1978)

# Niobium sputtering yield from ion argon bombardment

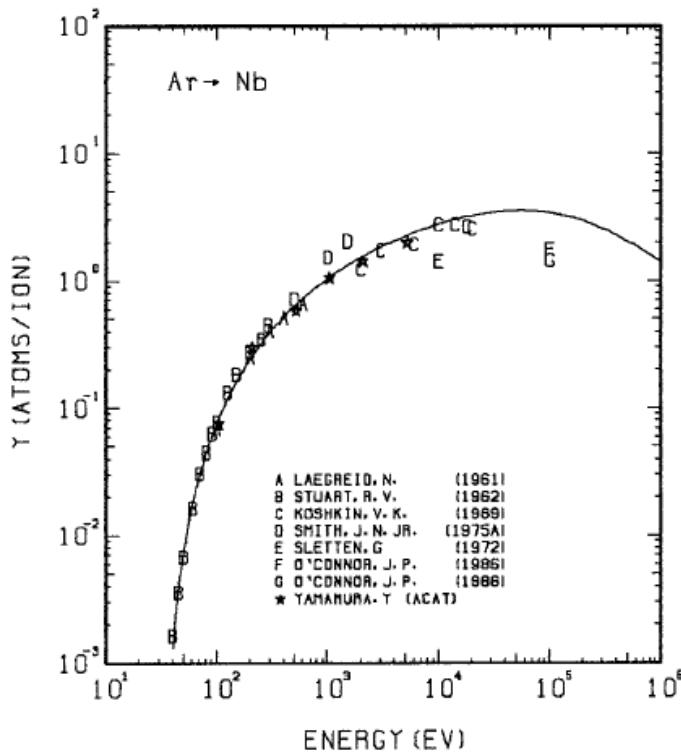
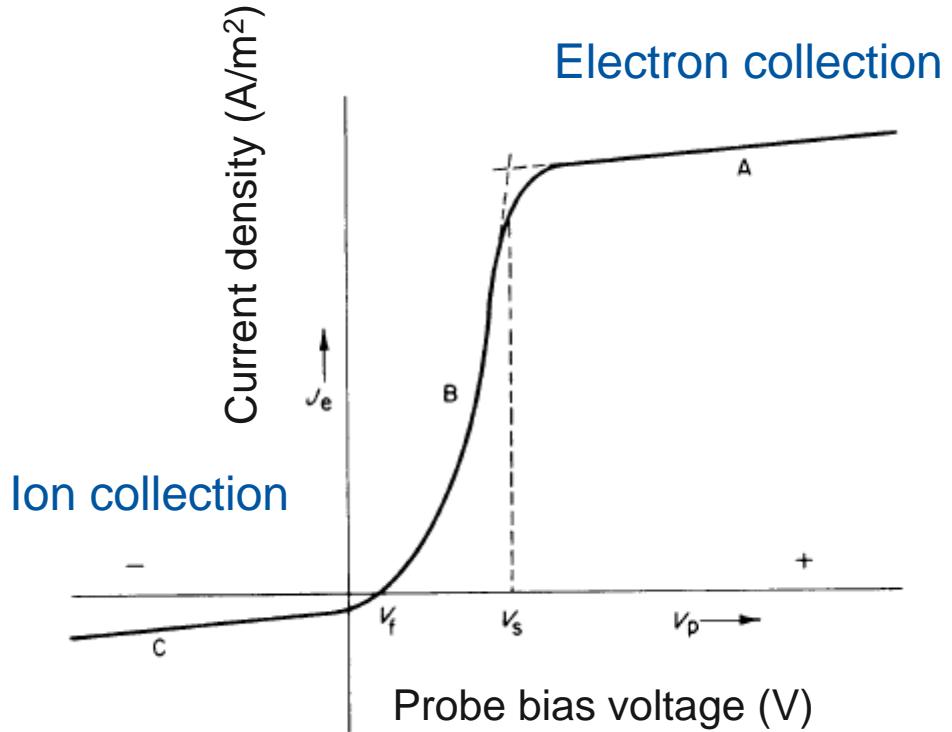


FIG. 157 ENERGY DEPENDENCE OF THE  
SPUTTERING YIELD OF NB WITH  $\text{Ar}^+$ .  
 $A = 2.33, Q = 0.93, U_s = 7.57 \text{ eV}, s = 2.80,$   
 $W = 0.35 \text{ eV}$ .

From Y. Yamamura, *Energy dependence of ion-induced sputtering yields from monoatomic solids at normal incidence*, Atomic Data and Nuclear Data Tables **62**, 149-253 (1996)

# Langmuir probe



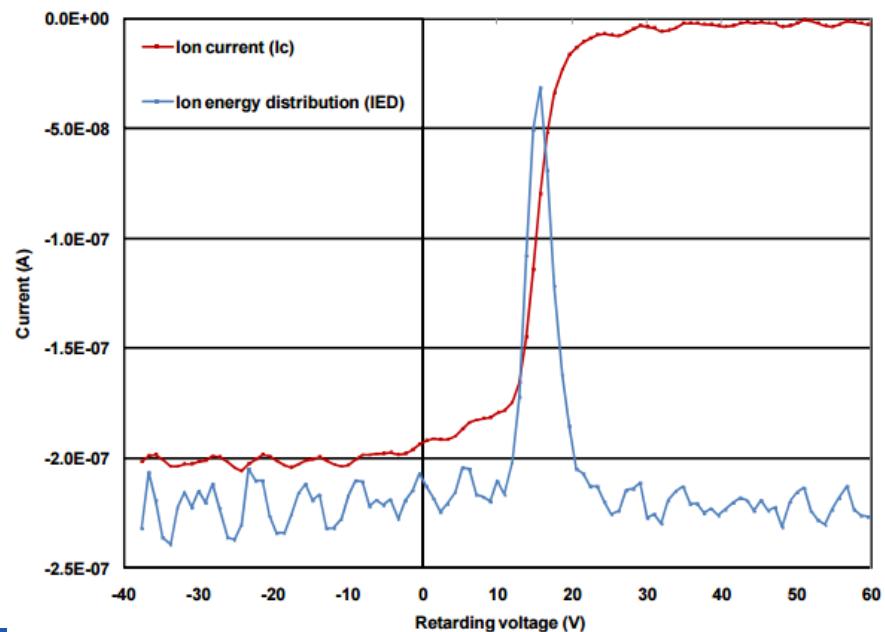
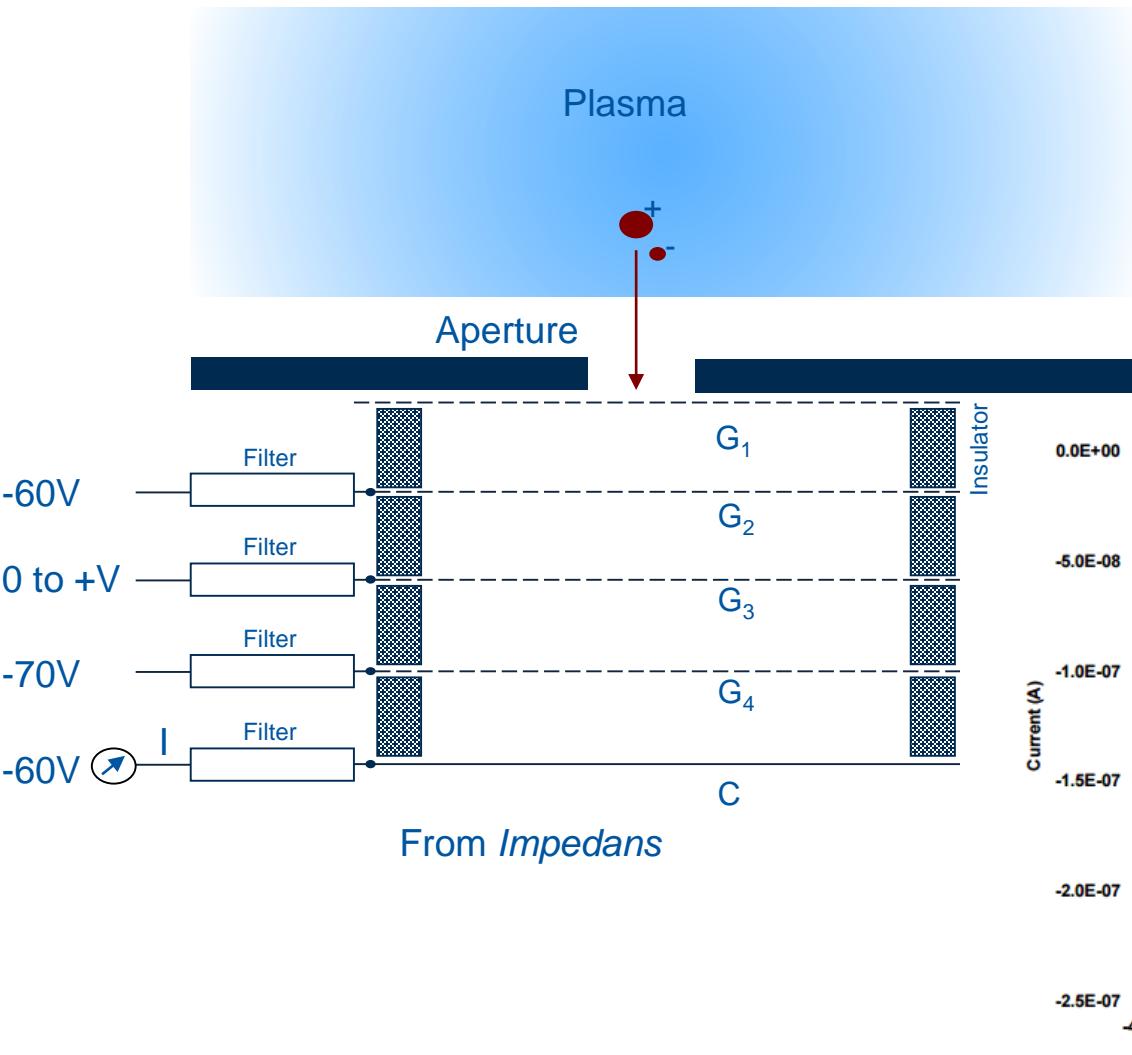
$V_f$  : floating potential  
 $V_s$  : plasma potential

$$I = I_{sat} \left[ 1 - \exp \frac{V - V_f}{T_e} \right]$$

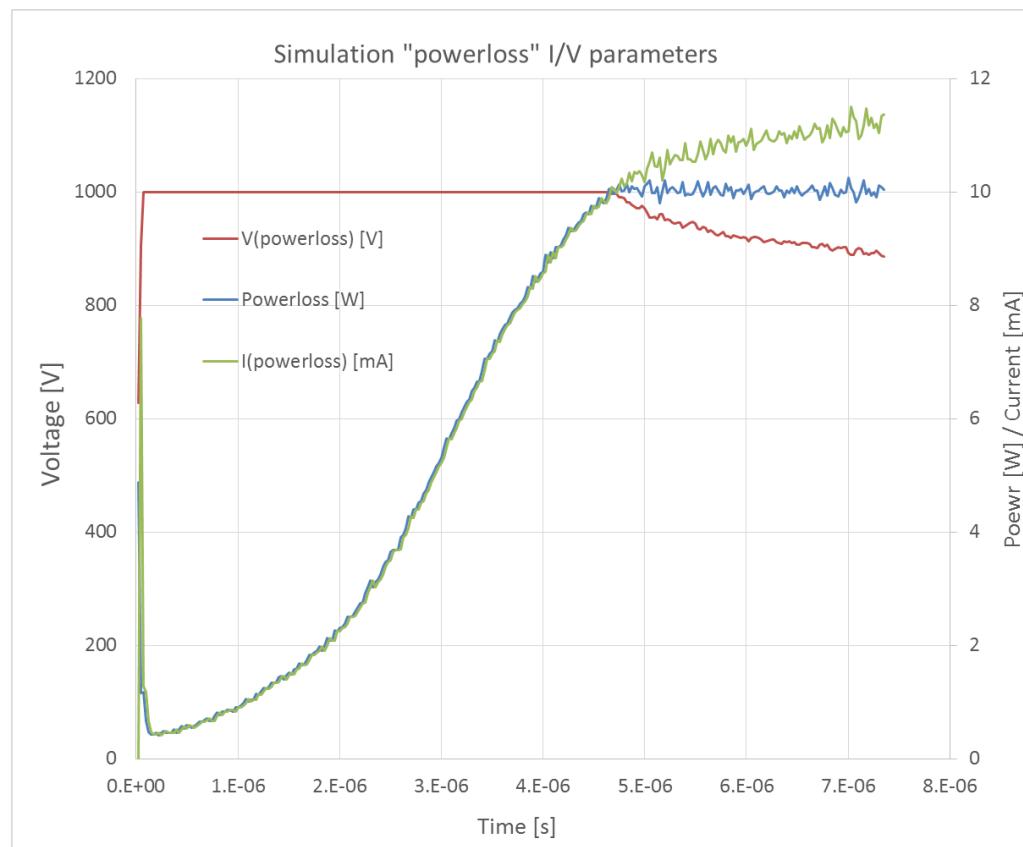
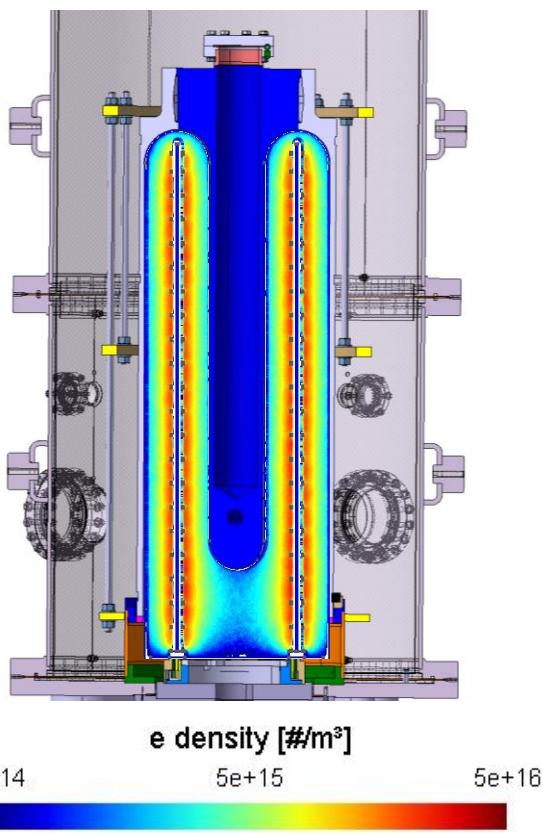
From  $I_{sat}$  and  $T_e$  :  $n_{\text{plasma}}$

Many thanks to Luigi and Spyros for manufacturing ☺

# RFEA

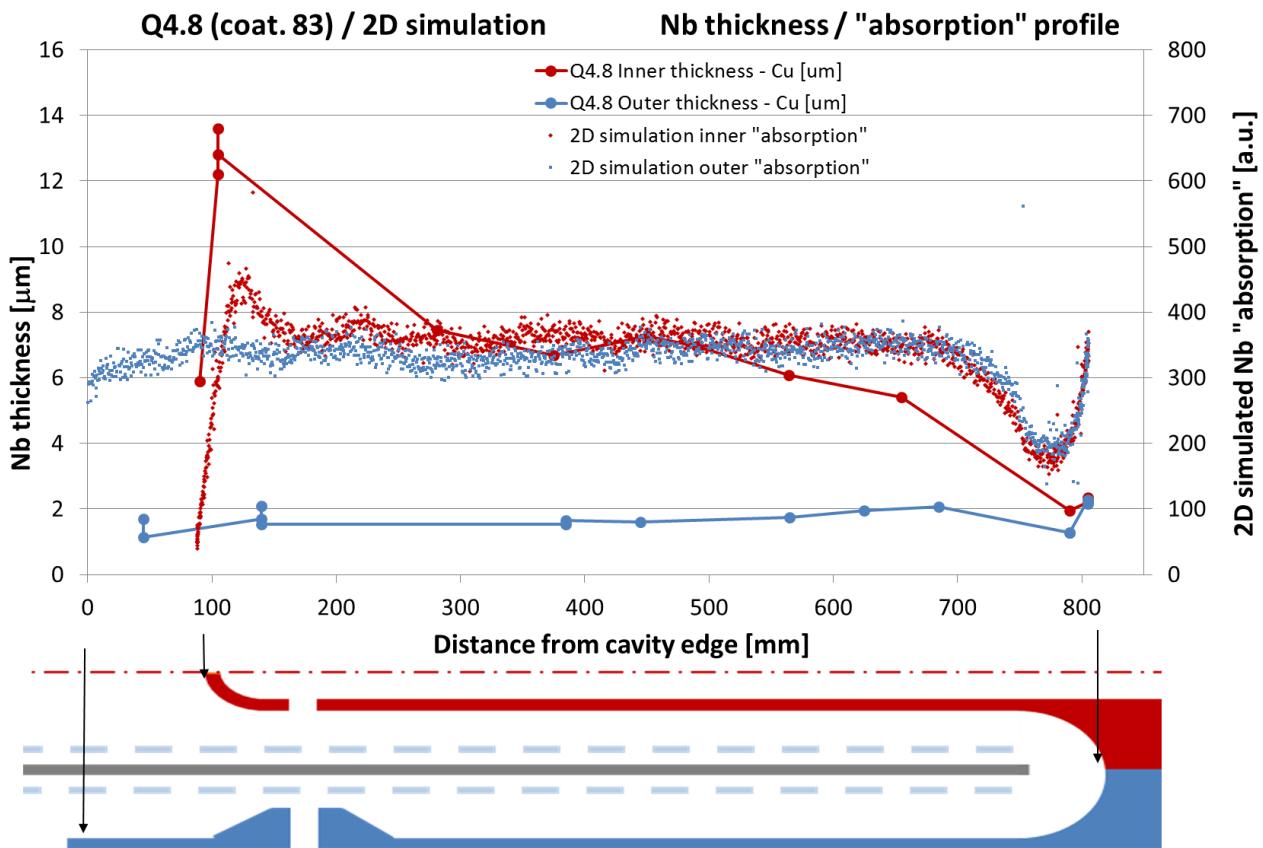
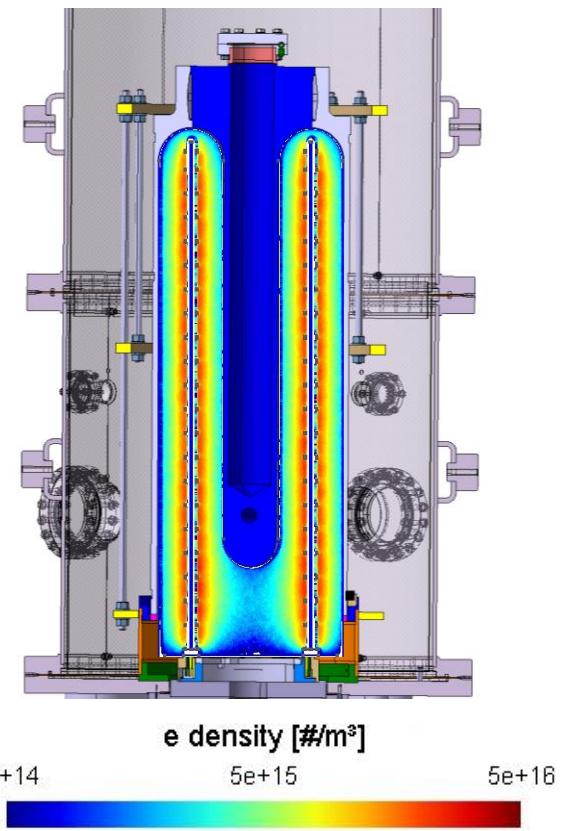


# HIE-ISOLDE 2D, very preliminary plasma and Nb transport simulation



- 2D slice of HIE-ISOLDE cavity with periodic boundary conditions
- Server connection lost after 72% of simulation, steady state not yet reached

# HIE-ISOLDE 2D, very preliminary plasma and Nb transport simulation



- 2D slice of HIE-ISOLDE cavity with periodic boundary conditions
- Encouraging start, but... we are still in the learning phase
- Need better understanding/optimization of code and parameters